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Main Specifications of Renesas Electronics' New RJK60S5DPK Power MOSFET

- Drain to Source Voltage (V_{DSS})
 - 600 V
- Gate to Source Voltage (V_{GSS})
 - 30 V
- Drain Current (I_D)
 - 20 A
- Static drain to source on state resistance ($R_{DS(on)}$)
 - 150 m Ω TYP. ($I_D = 10$ A, $V_{GSS} = 10$ V)
- Gate to drain charge (Q_{gd})
 - 6 nC TYP. ($I_D = 10$ A, $V_{GSS} = 10$ V)
- Gate to source cutoff voltage ($V_{GS(off)}$)
 - 3 V to 5 V
- Channel temperature (T_{ch})
 - +150 deg C
- Package
 - TO-3PSG